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### **N-Channel QFET® MOSFET**

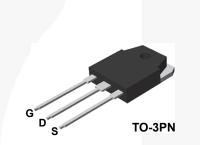
250 V, 62 A, 35 mΩ

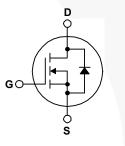
#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- + 62 A, 250 V,  $R_{DS(on)}$  = 35 m $\Omega$  (Max.) @ V\_{GS} = 10 V,  $I_{D}$  = 31 A
- Low Gate Charge (Typ. 100 nC)
- Low Crss (Typ. 63.5 pF)
- 100% Avalanche Tested





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQA62N25C	Unit		
V <sub>DSS</sub>	Drain-Source Voltage	250	V		
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)	62	А		
	- Continuous (T <sub>C</sub> = 100°C)	39			
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	248	А		
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V		
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	2300	mJ		
I <sub>AR</sub>	Avalanche Current (Note 1)	62	A		
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	29.8	mJ		
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns		
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)	298	W		
	- Derate above 25°C	2.38	W/°C		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C		
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C		

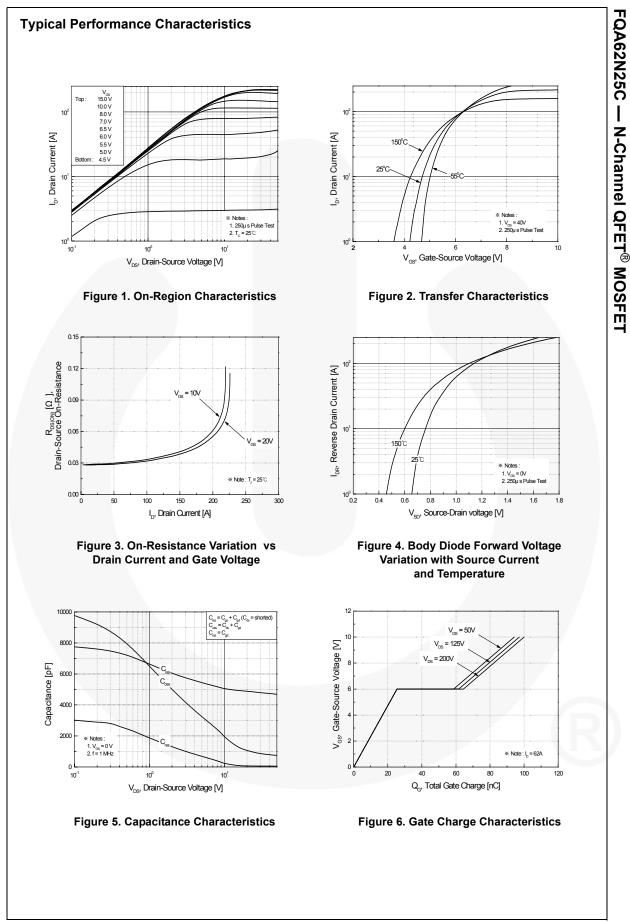
#### **Thermal Characteristics**

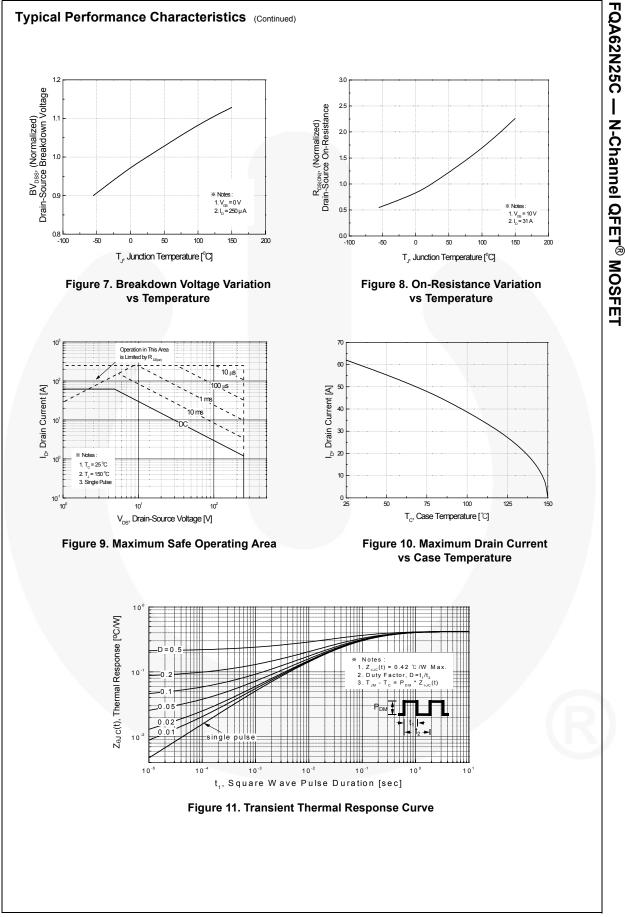
Symbol	Parameter	FQA62N25C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.42	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.24	°C/W	
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

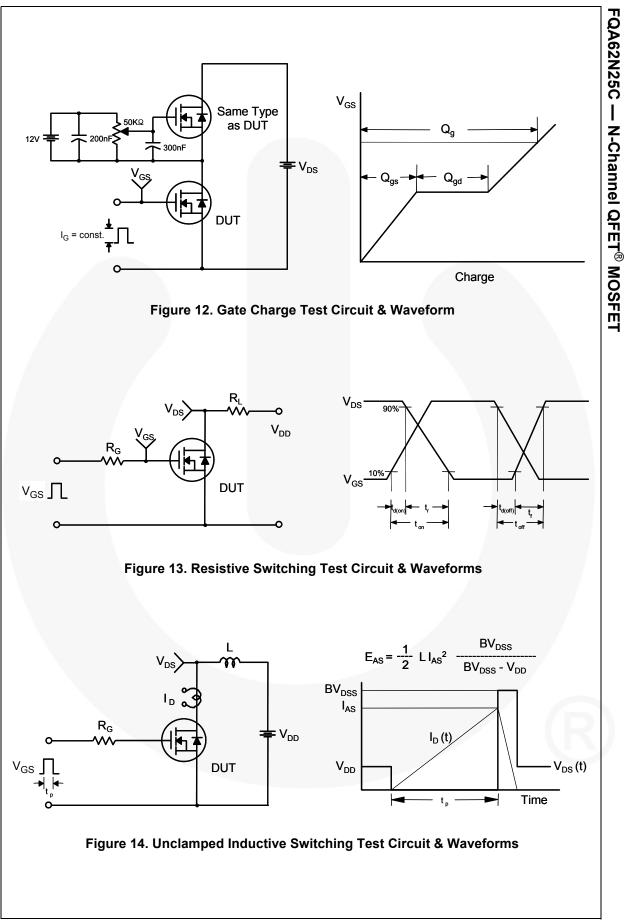
April 2014

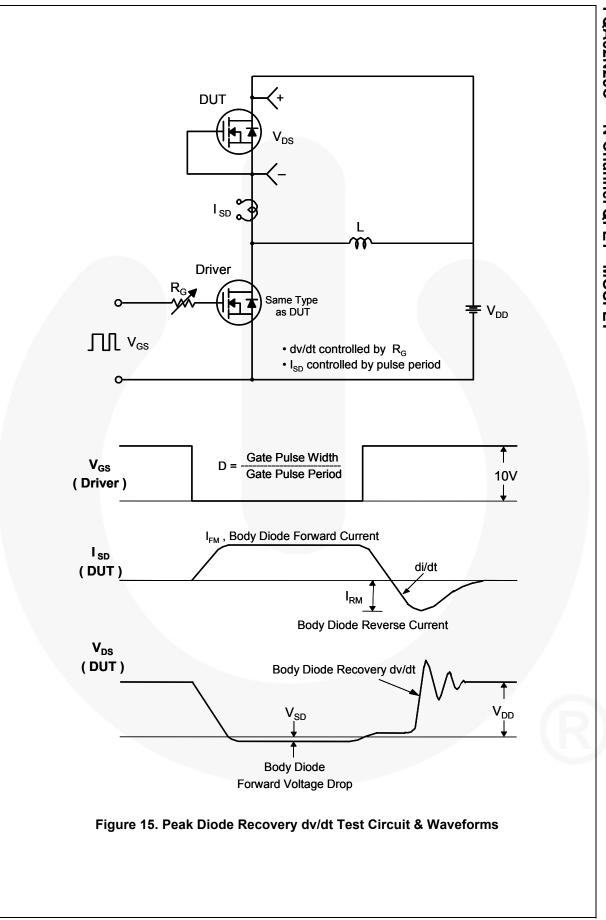
Part Nu	ımber	ber Top Mark		kage Packing Method Reel		Size	Tape Wi	idth	Quantity		
FQA62N25C FQA62N25C TO-		-			4	N/A		30 units			
loctri	cal Ch	aracteristics <b>1</b>	r. – 05°0 uml	ana athan	vice poted						
Symbol		Parameter	r <sub>c</sub> - 25 C uni	ess other	Test Con	ditions		Min.	Тур.	Max.	Unit
	rootori										
BV <sub>DSS</sub>	Drain S		200	Vec	$= 0 \sqrt{1_{\rm P}} = 2^{\mu}$	50 4		250			V
ABV <sub>DSS</sub>	Drain-Source Breakdown Voltage			V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA			250			v	
ΔT <sub>J</sub>			$I_D$ = 250 µA, Referenced to 25°C				0.28		V/°C		
DSS	Zero Gate Voltage Drain Current		$V_{\rm DS}$ = 250 V, $V_{\rm GS}$ = 0 V					10	μA		
			$V_{DS}$ = 200 V, $T_{C}$ = 125°C						100	μA	
GSSF	Gate-Bo	Gate-Body Leakage Current, Forward			= 30 V, V <sub>DS</sub> :					100	nA
GSSR	Gate-Bo	dy Leakage Current,	Reverse	V <sub>GS</sub> =	= -30 V, V <sub>DS</sub>	= 0 V				-100	nA
On Cha	racteris	stics									
V <sub>GS(th)</sub>	1	reshold Voltage		V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 2	250 μA	-	2.0		4.0	V
R <sub>DS(on)</sub>	Static Dr On-Resi	rain-Source		V <sub>GS</sub> =	= 10 V, I <sub>D</sub> = 31	A			0.029	0.035	Ω
9 <sub>FS</sub>		Forward Transconductance			= 40 V, I <sub>D</sub> = 3	81 A			55		S
10			_	00	· D						
		acteristics		1							
C <sub>iss</sub>	Input Ca	apacitance		V <sub>DS</sub> =	= 25 V, V <sub>GS</sub> =	= 0 V,			4830	6280	pF
C <sub>oss</sub>	Output 0	Capacitance		f = 1.0 MHz				945	1230	pF	
C <sub>rss</sub>	Reverse	Transfer Capacitance	е						63.5	83	pF
Switchi	ing Cha	racteristics									
d(on)		Delay Time	-	1					75	160	ns
·a(on) ·r		Rise Time			= 125 V, I <sub>D</sub> =	62 A,			395	800	ns
d(off)		Delay Time	-	R <sub>G</sub> =	25 Ω				245	500	ns
f		Fall Time	-	_			(Note 4)		335	680	ns
ີ ລ <sub>g</sub>		ite Charge		۱ <u>/</u> -	- 200 \/   -	62 4			100	130	nC
∽y ⊋ <sub>gs</sub>		ource Charge			= 200 V, I <sub>D</sub> = = 10 V	02 A,			25.5		nC
Q <sub>gd</sub>		ain Charge		VGS -	- 10 V		(Note 4)		39		nC
gu		ann annaige					. ,				
Drain-S	ource [	Diode Characteri	istics a	nd Ma	ximum R	atings					
s	Maximu	m Continuous Drain-S	Source Dic	e Diode Forward Current						62	Α
SM	Maximu	m Pulsed Drain-Source	ce Diode F	orward	Current					248	Α
V <sub>SD</sub>	Drain-Se	ource Diode Forward	Voltage	V <sub>GS</sub> =	= 0 V, I <sub>S</sub> = 62	2 A				1.5	V
t <sub>rr</sub>	Reverse	Recovery Time		V <sub>GS</sub> =	= 0 V, I <sub>S</sub> = 62	2 A,			340		ns
Q <sub>rr</sub>	Reverse	Recovery Charge		dl <sub>F</sub> /d	dt = 100 A/µs	6			4.77		μC
L = 0.96 mH I <sub>SD</sub> ≤ 62 A, c	H, I <sub>AS</sub> = 62 A, di/dt ≤ 300 A/	width limited by maximum ju $V_{DD} = 50 V$ , $R_G = 25 \Omega$ , start $\mu_S$ , $V_{DD} \le BV_{DSS}$ , starting $T_J$ ; of operating temperature.	ing T <sub>J</sub> = 25°C								

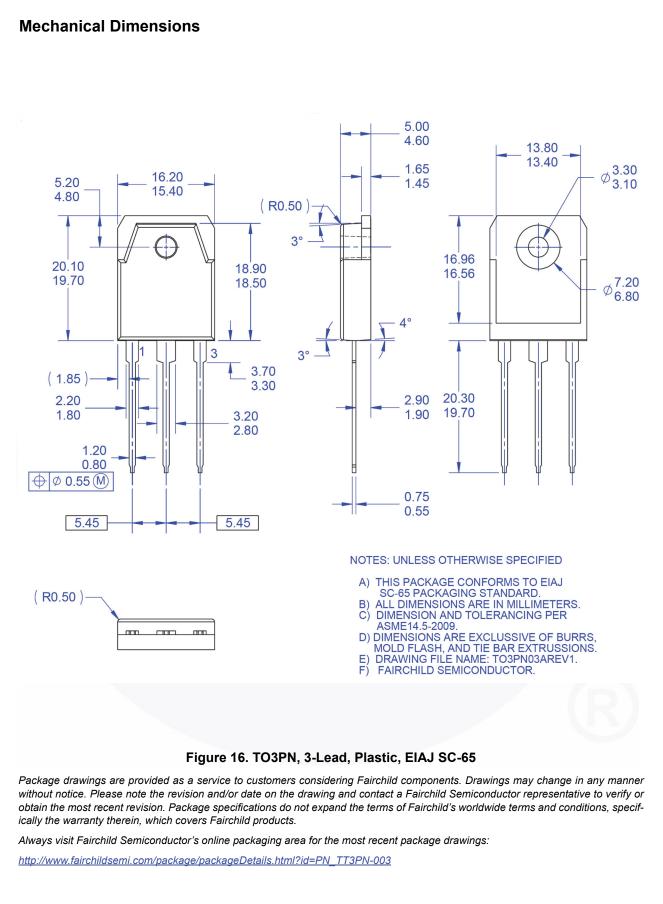
FQA62N25C — N-Channel QFET<sup>®</sup> MOSFET













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